Docket No.

243436US2SX

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF:

Keitaro IMAI, et al.

SERIAL NO: New Application

GAU:

FILED:

Herewith

EXAMINER:

FOR:

MANUFACTURING METHOD OF SEMICONDUCTOR DEVICE

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

COMMISSIONER FOR PATENTS ALEXANDRIA, VIRGINIA 22313

Applicant(s) wish to disclose the following information.

REFERENCES

The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references are attached, where required, as are either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references.

☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

- Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

- ☐ Each item of information contained in this information disclosure statement was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- □ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

Please charge any additional fees for the papers being filed herewith and for which no check or credit card payment is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

OBLON, SPIVAK, McCLELLAND, MAIER & NEUSTADT, P.C.

pivak Marvin 3

Registration No. 24,913

> Jámes D. Hamilton Registration No. 28,421

Customer Number

Tel. (703) 413-3000 Fax. (703) 413-2220 (OSMMN 05/03)

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LIST OF RELATED CASES

Docket Number	Serial or <u>Patent Number</u>	Filing or <u>Issue Date</u>	Inventor/ Applicant
PER CLIENT	6,459,111	10/01/02	NATORI et al.
PER CLIENT	10/222,813	08/19/02	NATORI et al.

DOCKET NO.: 243436US2SX

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SERIAL NO: New Application

FILED: HEREWITH

FOR: MANUFACTURING METHOD OF SEMICONDUCTOR DEVICE

STATEMENT OF RELEVANCY

Reference AA on Form PTO-1449:

This publication is referred to in the specification. See page 2, line 16.

Reference AB on Form PTO-1449:

This patent says capacitor structures made by damascene process. Dummy bottom electrode such as SrPu03 is formed by damascene process with wet etching. The technique suppresses process damage to capacitors.

Reference AW on Form PTO-1449:

AlrO₃ encapoulated capacitor and ferroelectric film no-etching processed structure using TiO₂ were presented in this paper. Original papers related to the technique are as follows.

- 1) Tech. Digest 1997 VLSI Tech Symp . pgs 139-140
- 2) Proc. SSDM, Tokyo. page 394 (1999)
- 3) Tech. Digest 2000 VLSI Tech Symp. pgs. 34-35

Form PTO 1449 U.S. DEPARTMENT OF COMMERCE (Modified) PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO.		SERIAL NO.						
		243436US2SX		New Application						
APPLICANT										
LIST OF	REFE	RENCES CITED BY API	PLICANT	Keitaro IMAI, et al.						
				FILING DATE		GROUP				
				Herewith						
U.S. PATENT DOCUMENTS										
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME CLASS		SUB FILING DATE CLASS IF APPROPRIATE				
	AA	6,153,460	11/28/00	Shigeo OHNISHI, et al.						
	AB	6,459,111	10/01/02	Katsuaki NATORI, et al.			,			
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			FO	REIGN PATENT DOCUMENTS						
		DOCUMENT NUMBER	DATE	COUNTRY		TRANSLATION				
	AO					YES	<u> </u>	NO		
	AP									
	AQ									
	AR									
	AS									
	АТ									
	AU									
	AV									
		OTHER RE	FERENCES (Including Author, Title, Date, Pertinent	t Pages, et	tc.)				
	AW	Kinam KIM, "High density stand alone-FRAM: Present and Future", INTEGRATED FERROELECTRICS, Vol. 36, 2001, pgs.21-39								
	AX									
	AY									
	AZ			Additional References sheet(s) attached						
Examiner				Date Considered						
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.										